IN THE CLAIMS

Please amend the claims as follows:

1 (Currently Amended): An electronic device comprising:

a first electrode including a metal oxide; and

a second electrode including an aluminum alloy film,

said second electrode being ~~directly contacted and~~ electrically connected to said first electrode,

wherein, in the contact interface between said aluminum alloy film and said first electrode, at least a part of alloy components constituting said aluminum alloy film exist as a precipitate extending through a concentrated alloy material of said aluminum alloy film, the concentrated alloy material existing at the contact interface between the metal oxide and the aluminum alloy film ~~or a concentrated layer~~,

wherein said aluminum alloy film includes at least one element ~~in a first range of at least 0.1 at %,~~ as a first alloy component X_1, the element being selected from the group consisting of Ag, Zn, Cu, and Ni,

said aluminum alloy film further includes, as a second alloy component X_2, at least one element selected from the group consisting of Nd and Y ~~in a second range of at least 0.1 at %,~~

wherein X_1 satisfy the following formula (I):

$$0.2 \leq 0.5 \times CX_1 + CX_2 \leq 4.5 \cdots (I)$$

wherein CX_1 represents the content (at %) of Ag, Zn, Cu, and Ni in the aluminum alloy, and CX_2 represents the content (at %) of Nd and Y in the aluminum alloy.

2 (Canceled).

3 (Previously Presented): The electronic device according to Claim 1, wherein said metal oxide comprises indium tin oxide or indium zinc oxide.

4 (Previously Presented): The electronic device according to Claim 1, wherein said aluminum alloy film contains at least Ni as its alloy component.

5-7 (Canceled).

8 (Original): The electronic device according to Claim 1, wherein said aluminum alloy film in which at least a part of the alloy components exist as a precipitate, and the electrical resistivity of said aluminum alloy film is not larger than 8 $\mu\Omega$•cm.

9 (Previously Presented): The electronic device according to Claim 1, wherein a particle of said precipitate has a size of more than 0.01 μm in major diameter and the number of the particles exceeds 0.13 particles/100 μm^2.

10 (Original): The electronic device according to Claim 1, wherein the area factor of said precipitate exceeds 0.5 %.

11 (Original): The electronic device according to Claim 4, wherein said aluminum alloy film containing Ni has a Ni-concentrated layer whose Ni content in a thickness region of 1 to 10 nm from the surface of said aluminum alloy film is not more than the Ni content inside the aluminum alloy film plus 8 at %.

12 (Previously Presented): The electronic device according to Claim 4, wherein a particle of said precipitate has a size of more than 0.05 μm in major diameter and the number of

the particles exceeds 21 particles/100 μm^2.

13 (Previously Presented): The electronic device according to Claim 4, wherein said aluminum alloy film further contains Nd and a particle of said precipitate has a size of more than 0.02 μm in major diameter and the number of the particles exceeds 33 particles/100 μm^2.

14 (Previously Presented): The electronic device according to Claim 4, wherein said aluminum alloy film further contains Nd and a particle of said precipitate has a size of more than 0.02 μm in major diameter and the number of the particles exceeds 33 particles/100 μm^2.

15 (Original): The electronic device according to Claim 1, wherein said electronic device comprises a thin film transistor arranged on a glass substrate and said thin film transistor is electrically connected to said first electrode through said aluminum alloy film.

16 (Original): The electronic device according to Claim 1, wherein said first electrode is a pixel electrode and said electronic device is a display device.

17 (Withdrawn): The method of manufacture of the electronic device according to Claim 1, comprising the step of forming a precipitate that contains at least a part of the alloy components contained in said aluminum alloy film by heating said aluminum alloy film formed on a substrate at a temperature of 150 to 400°C.

18 (Withdrawn): The method of manufacture according to Claim 17, wherein said aluminum alloy film is formed by a sputtering method.

19 (Withdrawn): The method of manufacture of the electronic device according to Claim 1, comprising the steps of:

forming said aluminum alloy film on a substrate;

forming an insulating film on said aluminum alloy film;

processing the insulating film by hole etching; and

etching said aluminum alloy film by 1 to 200 nm from the surface thereof successively after the hole etching, whereby a precipitate containing at least a part of the alloy components contained in said aluminum alloy film is exposed partially.

20 (Withdrawn): The method of manufacture according to Claim 19, wherein the etching is performed by dry etching using a gas capable of etching said aluminum alloy film.

21 (Withdrawn): The method of manufacture according to Claim 19, wherein the etching is performed by wet etching using a chemical capable of etching said aluminum alloy film.

22 (Withdrawn): The method of manufacture according to Claim 19, wherein a photoresist stripper including not less than 5 wt% amine compound is used in cleaning of the aluminum alloy film after the etching.

23-25 (Canceled).

26 (Currently Amended): An electronic device comprising:

a first electrode including a metal oxide; and

a second electrode including an aluminum alloy film, said second electrode being

~~directly contacted and~~ electrically connected to said first electrode,

wherein, in the contact interface between said aluminum alloy film and said first electrode, at least a part of alloy components constituting said aluminum alloy film exist as a precipitate extending through a concentrated alloy material of said aluminum alloy film, the concentrated alloy material existing at the contact interface between the metal oxide and the aluminum alloy film ~~or a concentrated layer~~,

wherein said aluminum alloy film includes at least one element ~~in a first range of at least 0.1 at%,~~ as a first alloy component Y_1, the element being selected from the group consisting of Ag, Zn, Cu, and Ni,

said aluminum alloy film further includes, as a second alloy component Y_2, at least one element selected from the group consisting of Fe, and Co ~~in a second range of at least 0.1 at%~~,

wherein satisfy the following formula (II):

$$0.4 \leq CY_1 + CY_2 \leq 6 \cdots \text{(II)}$$

wherein CY_1 represents the content of Ag, Zn, Cu, and Ni in the aluminum alloy (at%), and CY_2 represents the content of Fe and Co in the aluminum alloy (at%).

27 (Previously Presented): The electronic device according to Claim 26, wherein said metal oxide is indium tin oxide or indium zinc oxide.

28 (Previously Presented): The electronic device according to Claim 26, wherein said aluminum alloy film contains at least Ni as its alloy component.

29 (Previously Presented): The electronic device according to Claim 26, wherein said aluminum alloy film in which at least a part of the alloy components exist as a precipitate, and the electrical resistivity of said aluminum alloy film is not larger than 8 $\mu\Omega \cdot$cm.

30 (Previously Presented): The electronic device according to Claim 26, wherein a particle of said precipitate has a size of more than 0.01 μm in major diameter and the number of the particles exceeds 0.13 particles/100 μm^2.

31 (Previously Presented): The electronic device according to Claim 26, wherein the area factor of said precipitate exceeds 0.5 %.

32 (Previously Presented): The electronic device according to Claim 28, wherein said aluminum alloy film containing Ni has a Ni-concentrated layer whose Ni content in a thickness region of 1 to 10 nm from the surface of said aluminum alloy film is not more than the Ni content inside the aluminum alloy film plus 8 at%.

33 (Previously Presented): The electronic device according to Claim 28, wherein a particle of said precipitate has a size of more than 0.05 μm in major diameter and the number of the particles exceeds 21 particles/100 μm^2.

34 (Previously Presented): The electronic device according to Claim 28, wherein said aluminum alloy film further contains Nd and a particle of said precipitate has a size of more than 0.02 μm in major diameter and the number of the particles exceeds 33 particles/100 μm^2.

35 (Previously Presented): The electronic device according to Claim 28, wherein said aluminum alloy film further contains Nd and a particle of said precipitate has a size of more than 0.02 μm in major diameter and the number of the particles exceeds 33 particles/100 μm^2.

36 (Previously Presented): The electronic device according to Claim 26, wherein said electronic device comprises a thin film transistor arranged on a glass substrate and said thin film transistor is electrically connected to said first electrode through said aluminum alloy film.

37 (Previously Presented): The electronic device according to Claim 26, wherein said first electrode is a pixel electrode and said electronic device is a display device.

38 (Previously Presented): An electronic device comprising:

a first electrode including a metal oxide; and

a second electrode including an aluminum alloy film, said second electrode being directly contacted and electrically connected to said first electrode,

wherein, in the contact interface between said aluminum alloy film and said first electrode, at least a part of alloy components constituting said aluminum alloy film exist as a precipitate, wherein a particle of said precipitate has a size of more than 0.01 μm in major diameter and the number of the particles exceeds 0.13 particles/100 μm^2.

39 (Previously Presented): The electronic device according to Claim 38, wherein said aluminum alloy film contains at least one element in the range of 0.1 to 6 at % as its alloy component, the element being selected from the group consisting of Au, Ag, Zn, Cu, Ni, Sr, Sm, Ge, and Bi.

40 (Previously Presented): The electronic device according to Claim 39, wherein said aluminum alloy film further contains, as its another alloy component, at least one element selected from the group consisting of Nd, Y, Fe, and Co in the range of 0.1 to 6 at %.

41 (Previously Presented): The electronic device according to Claim 38, wherein said metal oxide is indium tin oxide or indium zinc oxide.

42 (Previously Presented): The electronic device according to Claim 39, wherein said aluminum alloy film contains at least Ni as its alloy component.

43 (Previously Presented): The electronic device according to Claim 38, the electrical resistivity of said aluminum alloy film is not larger than 8 $\mu\Omega$•cm.

44 (Previously Presented): The electronic device according to Claim 38, wherein the area factor of said precipitate exceeds 0.5 %.

45 (Previously Presented): The electronic device according to Claim 42, wherein a particle of said precipitate has a size of more than 0.05 μm in major diameter and the number of the particles exceeds 21 particles/100 μm^2.

46 (Previously Presented): The electronic device according to Claim 42, wherein said aluminum alloy film further contains Nd and a particle of said precipitate has a size of more than 0.02 μm in major diameter and the number of the particles exceeds 33 particles/100 μm^2.

47 (Previously Presented): The electronic device according to Claim 42, wherein said aluminum alloy film further contains Nd and a particle of said precipitate has a size of more than 0.02 μm in major diameter and the number of the particles exceeds 33 particles/100 μm^2.

48 (Previously Presented): The electronic device according to Claim 38, wherein said

electronic device comprises a thin film transistor arranged on a glass substrate and said thin film transistor is electrically connected to said first electrode through said aluminum alloy film.

49 (Previously Presented): The electronic device according to Claim 38, wherein said first electrode is a pixel electrode and said electronic device is a display device.

50 (Previously Presented): An electronic device comprising:

a first electrode including a metal oxide; and

a second electrode including an aluminum alloy film, said second electrode being directly contacted and electrically connected to said first electrode,

wherein, in the contact interface between said aluminum alloy film and said first electrode, at least a part of alloy components constituting said aluminum alloy film exist as a concentrated layer,

wherein said aluminum alloy film contains Ni in the range of 0.1 to 6 at % as its alloy component,

wherein said aluminum alloy film containing Ni has a Ni-concentrated layer whose Ni content in a thickness region of 1 to 10 nm from the surface of said aluminum alloy film is not more than the Ni content inside the aluminum alloy film plus 8 at%.

51 (Previously Presented): The electronic device according to Claim 50, wherein said aluminum alloy film further contains, as its another alloy component, at least one element selected from the group consisting of Nd, Y, Fe, and Co in the range of 0.1 to 6 at%.

52 (Previously Presented): The electronic device according to Claim 50, wherein said metal oxide is indium tin oxide or indium zinc oxide.

53 (Previously Presented): The electronic device according to Claim 50, wherein said electronic device comprises a thin film transistor arranged on a glass substrate and said thin film transistor is electrically connected to said first electrode through said aluminum alloy film.

54 (Previously Presented): The electronic device according to Claim 50, wherein said first electrode is a pixel electrode and said electronic device is a display device.

55 (Previously Presented): An electronic device comprising:

a first electrode including a metal oxide; and

a second electrode including an aluminum alloy film, said second electrode being directly contacted and electrically connected to said first electrode,

wherein, in the contact interface between said aluminum alloy film and said first electrode, at least a part of alloy components constituting said aluminum alloy film exist as a precipitate, wherein said aluminum alloy film contains Ni in the range of 0.1 to 6 at% as its alloy component,

wherein a particle of said precipitate has a size of more than 0.05 μm in major diameter and the number of the particles exceeds 21 particles/100 μm^2.

56 (Previously Presented): The electronic device according to Claim 55, wherein said aluminum alloy film further contains, as its another alloy component, at least one element selected from the group consisting of Nd, Y, Fe, and Co in the range of 0.1 to 6 at%.

57 (Previously Presented): The electronic device according to Claim 55, wherein said metal oxide is indium tin oxide or indium zinc oxide.

58 (Previously Presented): The electronic device according to Claim 55, wherein said electronic device comprises a thin film transistor arranged on a glass substrate and said thin film transistor is electrically connected to said first electrode through said aluminum alloy film.

59 (Previously Presented): The electronic device according to Claim 55, wherein said first electrode is a pixel electrode and said electronic device is a display device.

60 (Previously Presented): An electronic device comprising:

a first electrode including a metal oxide; and

a second electrode including an aluminum alloy film, said second electrode being directly contacted and electrically connected to said first electrode,

wherein, in the contact interface between said aluminum alloy film and said first electrode, at least a part of alloy components constituting said aluminum alloy film exist as a precipitate,

wherein said aluminum alloy film contains Ni in the range of 0.1 to 6 at% as its alloy component,

wherein said aluminum alloy film further contains Nd and a particle of said precipitate has a size of more than 0.02 μm in major diameter and the number of the particles exceeds 33 particles/100 μm^2.

61 (Previously Presented): The electronic device according to Claim 60, wherein said metal oxide is indium tin oxide or indium zinc oxide.

62 (Previously Presented): The electronic device according to Claim 60, wherein said

electronic device comprises a thin film transistor arranged on a glass substrate and said thin film transistor is electrically connected to said first electrode through said aluminum alloy film.

63 (Previously Presented): The electronic device according to Claim 60, wherein said first electrode is a pixel electrode and said electronic device is a display device.